

One-cell Li-ion Battery Protection IC with High-accuracy Overcurrent Detection

No.EA-574-210421

OVERVIEW

The R5612L is a one-cell Li-ion / polymer battery protection IC providing overcharge, overdischarge and charge / discharge overcurrent detections. Major features of this device include charge / discharge overcurrent detectors with high-accuracy of ± 1.0 mV.

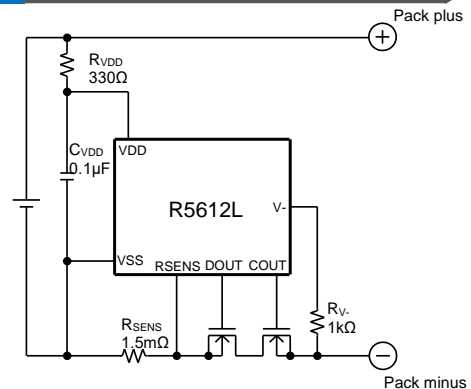
KEY BENEFITS

- Lower-resistance of Sense Resistor by Overcurrent Detector with Lower-voltage and High-accuracy: Achieving Heat Reduction on Board
- Low Consumption Current and Low Standby Current: Achieving Longer Driving Time with A Battery of Small Capacity

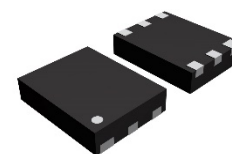
KEY SPECIFICATIONS

- Supply Current
 - Normal Mode: Typ. $2.5 \mu\text{A}$ / Max. $4.8 \mu\text{A}$
(Only when selected 0 V Battery Charging "Inhibition" and Discharge Overcurrent Detection with Two-level), Typ. $2.0 \mu\text{A}$ / Max. $4.0 \mu\text{A}$
(Except for the above selection)
 - Standby Mode: Max. $0.2 \mu\text{A}$ ($V_{\text{DET}2}$: Auto Release type)
Max. $0.04 \mu\text{A}$ ($V_{\text{DET}2}$: Latch type)
- Detector Selectable Range and Accuracy
 - Overcharge detection voltage ($V_{\text{DET}1}$): 4.2 V to 4.7 V , $\pm 20 \text{ mV}$,
 - Overdischarge detection voltage ($V_{\text{DET}2}$): 2.1 V to 3.2 V , $\pm 35 \text{ mV}$
 - Discharge overcurrent detection voltage1 ($V_{\text{DET}31}$):
 0.0070 V to 0.0330 V , $\pm 1 \text{ mV}$
 - Discharge overcurrent detection voltage2 ($V_{\text{DET}32}$):
 0.011 V to 0.060 V , $\pm 2 \text{ mV}$
 - Charge overcurrent detection voltage ($V_{\text{DET}4}$):
 -0.0070 V to -0.0300 V , $\pm 1 \text{ mV}$
 - Short-circuit detection voltage ($V_{\text{SHORT}1}$):
 $0.030 \text{ V} \leq V_{\text{SHORT}1} \leq 0.120 \text{ V}$, $\pm 4 \text{ mV}$
 $0.120 \text{ V} < V_{\text{SHORT}1} \leq 0.200 \text{ V}$, $\pm 5 \text{ mV}$
- 0 V Battery Charging selectable: Permission / Inhibition
0 V charge inhibition voltage: $1.000 / 1.200$
- Overcharge / Overdischarge Release Voltage Type selectable:
Auto Release / Latch
- Discharge Overcurrent Release Voltage Type selectable:
Auto Release1 ($V_{-} = V_{\text{DD}} \times 0.8\text{V}$) / Auto Release2 ($V_{-} = 0.1\text{V}$)
- Discharge Overcurrent Detection having two-level voltage detection ($V_{\text{DET}31}/V_{\text{DET}32}$) selectable: Enable / Disable

TYPICAL APPLICATION CIRCUIT



PACKAGE



DFN1814-6C

1.4 mm x 1.8 mm x 0.4 mm

APPLICATIONS

- Smart Phone, Tablet PC
- Game, Hearing Aid

SELECTION GUIDE

Set Output Voltages, Delay Times, and Optional Functions are user-selectable.

Selection Guide

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R5612Lxxx\$*-TR	DFN1814-6C	5,000 pcs	Yes	Yes

xxx: Specify a code combining the following set voltages. Refer to *Product Code List* for details.

Overcharge Detection Voltage (V_{DET1}): 4.2 V to 4.7 V in 5 mV step
 Overcharge Release Voltage (V_{REL1}): 4.0 V to 4.5 V in 5 mV step
 Overdischarge Detection Voltage (V_{DET2}): 2.1 V to 3.2 V in 50 mV step
 Overdischarge Release Voltage (V_{REL2}): 2.3 V to 3.2 V in 50 mV step
 Discharge Overcurrent Detection Voltage 1 (V_{DET31}) ⁽¹⁾: 0.0070 V to 0.0330 V in 0.5 mV step
 Discharge Overcurrent Detection Voltage 2 (V_{DET32}) ⁽¹⁾: 0.011 V to 0.060 V in 0.5 mV step
 Short-Circuit Detection Voltage (V_{SHORT1}) ⁽¹⁾: 0.030 V to 0.200 V in 5 mV step
 Charge Overcurrent Detection Voltage (V_{DET4}): -0.0070 V to -0.0300 V in 0.5mV step
 0 V Charge Inhibition Voltage (V_{NOCHG}): 1.000 V / 1.200 V

\$: Specify a code combining the following delay times. Refer to *Delay Time Code Table* for details.

Overcharge Detection / Release Delay Time (t_{VDET1} / t_{VREL1})
 Overdischarge Detection / Release Delay Time (t_{VDET2} / t_{VREL2})
 Discharge Overcurrent Delay Time1/2 (t_{VDET31} / t_{VDET32})
 Discharge Overcurrent Release Delay Time (t_{VREL3})
 Charge Overcurrent Detection / Release Delay Time (t_{VDET4} / t_{VREL4})

Delay Time Code Table

Code	Delay Time [ms]									
	t_{VDET1}	t_{VREL1}	t_{VDET2}	t_{VREL2}	t_{VDET31}	t_{VDET32}	t_{VREL3}	t_{VDET4}	t_{VREL4}	t_{SHORT}
A	1024	1.2	64	1.2	3584	16	8.5	17	4	0.28
B	1024	16	64	1.2	512	-	8.5	17	4	0.28
C	1024	16	20	1.2	12	-	8.5	17	4	0.28
D	1024	16	20	1.2	4096	16	8.5	17	4	0.28
E	1024	1.2	64	1.2	128	-	8.5	64	4	0.28
F	1024	1.2	64	1.2	256	-	8.5	17	4	0.28
G	1024	1.2	64	1.2	512	-	8.5	17	4	0.28

⁽¹⁾ When selecting each set output voltage of V_{DET31} , V_{DET32} and V_{SHORT1} , keep from overlapping among them in consideration of their output voltage accuracy. Especially, V_{SHORT1} should be higher than 7.5 mV from V_{DET31} and V_{DET32} .

*: Specify a code combining the following functions. Refer to *Function Code Table* for details.

Function Code Table

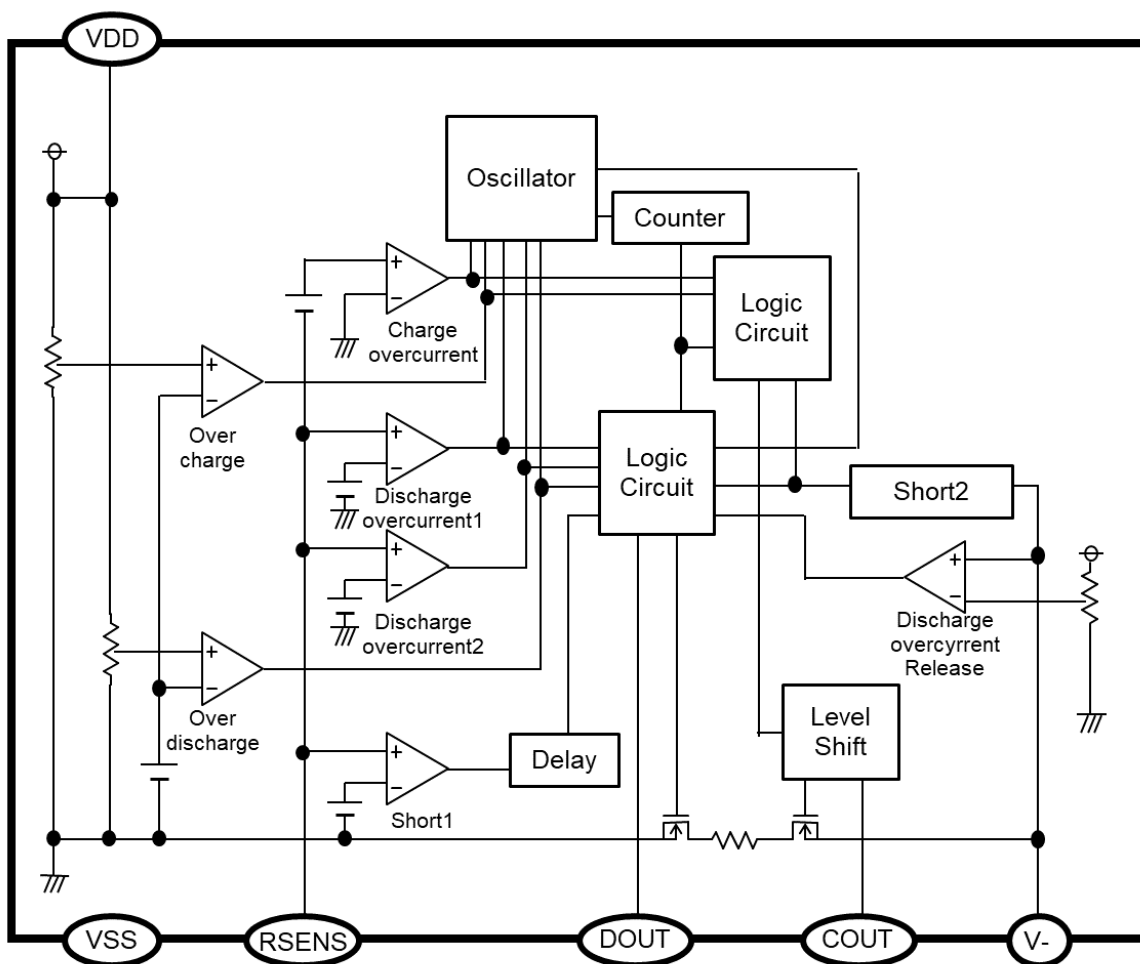
Code	Overcharge Release	Overdischarge Release	Discharge Overcurrent			0 V Battery Charging (Inhibition Voltage: V _{NOCHG})
			Release	Detection		
				V _{DET31}	V _{DET32}	
A	Auto Release	Auto Release	Auto Release1	Available (≤ 0.0115 V)	Available	Permission
B	Auto Release	Auto Release	Auto Release1	Available (≤ 0.0115 V)	Unavailable	Permission
D	Latch	Latch	Auto Release2	Available (≤ 0.0115 V)	Available	Inhibition (1.000 V)
E	Auto Release	Auto Release	Auto Release1	Available (≤ 0.0115 V)	Unavailable	Inhibition (1.200 V)
G	Auto Release	Auto Release	Auto Release1	Available (> 0.0115 V)	Available	Permission
H	Auto Release	Auto Release	Auto Release1	Available (> 0.0115 V)	Unavailable	Inhibition (1.200 V)

Product Code List

Product Code Table

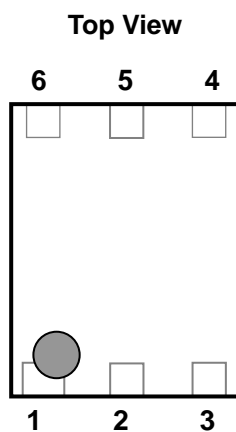
Product Name (Code)	Set Voltage [V]								
	V _{DET1}	V _{REL1}	V _{DET2}	V _{REL2}	V _{DET31}	V _{DET32}	V _{SHORT1}	V _{DET4}	V _{NOCHG}
R5612L102AA	4.500	4.350	2.100	2.300	0.0105	0.0150	0.0400	-0.0180	—
R5612L103AG	4.500	4.350	2.100	2.300	0.0150	0.0195	0.0420	-0.0180	—
R5612L104AA	4.530	4.330	2.350	2.550	0.0105	0.0150	0.0420	-0.0150	—
R5612L105AA	4.550	4.350	2.100	2.300	0.0105	0.0150	0.0420	-0.0180	—
R5612L106AG	4.530	4.330	2.350	2.550	0.0210	0.0330	0.0800	-0.0240	—
R5612L107AG	4.550	4.350	2.100	2.300	0.0210	0.0330	0.0800	-0.0300	—
R5612L109EH	4.475	4.275	2.500	2.900	0.0210	—	0.0800	-0.0210	1.20
R5612L114AG	4.580	4.380	2.350	2.550	0.0330	0.0550	0.1250	-0.0250	—
R5612L119AG	4.525	4.425	2.500	2.600	0.0200	0.0300	0.0750	-0.0250	—
R5612L120BB	4.500	4.350	2.100	2.300	0.0105	—	0.0400	-0.0180	—
R5612L120CB	4.500	4.350	2.100	2.300	0.0105	—	0.0400	-0.0180	—
R5612L120CE	4.500	4.350	2.100	2.300	0.0105	—	0.0400	-0.0180	1.20
R5612L121DD	4.500	—	2.100	—	0.0105	0.0150	0.0400	-0.0180	1.00
R5612L122FH	4.600	4.350	2.600	2.900	0.0120	—	0.0300	-0.0160	1.20
R5612L123GH	4.650	4.400	2.100	2.400	0.0150	—	0.0400	-0.0190	1.20

BLOCK DIAGRAM



R5612L Block Diagram

PIN DESCRIPTION



R5612L (DFN1814-6C) Pin Configuration

R5612L Pin Description

Pin No	Symbol	Pin Description
1	V ₋	Charge negative input pin
2	COUT	Charge detection output pin, CMOS output
3	DOUT	Discharge detection output pin, CMOS output
4	VSS	Ground pin for the IC
5	VDD	Power supply pin, the substrate level of the IC
6	RSENS	Overcurrent detection input pin

ABSOLUTE MAXIMUM RATINGS

(Ta = 25°C, V_{SS} = 0V)

Symbol	Item	Rating	Unit
V _{DD}	Supply voltage	-0.3 to 12	V
V-	V- pin input voltage	V _{DD} -30 to V _{DD} +0.3	V
V _{RSENS}	RSENS pin input voltage	V _{SS} -0.3 to V _{DD} +0.3	V
V _{COUT}	COUT pin output voltage	V _{DD} -30 to V _{DD} +0.3	V
V _{DOUT}	DOUT pin output voltage	V _{SS} -0.3 to V _{DD} +0.3	V
P _D	Power Dissipation	Refer to Appendix "Power Dissipation"	
T _j	Junction Temperature Range	-40 to 125	°C
T _{stg}	Storage Temperature Range	-55 to 125	°C

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operations at or over these absolute maximum ratings are not assured.

RECOMMENDED OPERATING CONDITION

Symbol	Item	Rating	Unit
V _{DD}	Operating Input Voltage	1.5 to 5.0	V
T _a	Operating Temperature Range	-40 to 85	°C

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

ELECTRICAL CHARACTERISTICS

R5612LxxxXX Electrical Characteristics

(Ta = 25°C)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	Circuit (1)	
V _{DD1}	Operating input voltage	V _{DD} -V _{SS}	1.5		5.0	V	A	
V _{STCHG}	Minimum charging voltage for 0 V-battery charger ⁽²⁾	V _{DD} -V ₋ , V _{DD} -V _{SS} = 0 V			1.8	V	A	
V _{NOCHG}	0 V-battery Charging Inhibition Voltage ⁽³⁾	V _{DD} -V _{SS} , V _{DD} -V ₋ = 4 V	V _{NOCHG} -0.25	V _{NOCHG}	V _{NOCHG} +0.25	V	A	
V _{DET1}	Overcharge detection voltage	R1 = 330Ω	V _{DET1} -0.020	V _{DET1}	V _{DET1} +0.020	V	B	
V _{REL1}	Overcharge release voltage	R1 = 330Ω	V _{REL1} -0.045	V _{REL1}	V _{REL1} +0.045	V	B	
t _{VDET1}	Overcharge detection delay time	V _{DD} = 3.6 V → V _{DET1} +0.1 V	t _{VDET1} ×0.75	t _{VDET1}	t _{VDET1} ×1.30	ms	C	
t _{VREL1}	Overcharge release delay time	V _{DD} = 4.8 V →	t _{VREL1} = 1.2ms	0.7	1.2	2.5	ms	C
		V _{REL1} -0.1 V	t _{VREL1} = 16ms	11.2	16	20.8		
V _{DET2}	Overdischarge detection voltage	Detect falling edge of supply voltage	V _{DET2} -0.035	V _{DET2}	V _{DET2} +0.035	V	D	
V _{REL2}	Overdischarge release voltage	Detect rising edge of supply voltage	V _{REL2} -0.055	V _{REL2}	V _{REL2} +0.095	V	E	
t _{VDET2}	Overdischarge detection delay time	V _{DD} = V _{DET2} +0.15V → V _{DET2} -0.1V	t _{VDET2} ×0.75	t _{VDET2}	t _{VDET2} ×1.30	ms	D	
t _{VREL2}	Overdischarge release delay time	V _{DD} = V _{DET2} -0.2V → V _{REL2} +0.25V	0.9	1.2	1.7	ms	E	
V _{CHGDET}	Charger Connection Detection Voltage	V _{DD} = V _{DET2} +0.020V, V _{RSENS} = 0 V	0.500	0.800	1.100	V	A	
V _{DET31}	Discharge overcurrent detection voltage 1	V _{DD} = 3.6 V, V ₋ = V _{RSENS}	V _{DET31} -0.0010	V _{DET31}	V _{DET31} +0.0010	V	F	
t _{VDET31}	Discharge overcurrent 1 detection delay time	V _{DD} = 3.6 V, V _{RSENS} = 0 V → V _{DET31} +0.005 V V ₋ = V _{RSENS}	t _{VDET31} ×0.75	t _{VDET31}	t _{VDET31} ×1.30	ms	F	
V _{DET32}	Discharge overcurrent detection voltage 2	V _{DD} = 3.6 V, V ₋ = V _{RSENS}	V _{DET32} -0.002	V _{DET32}	V _{DET32} +0.002	V	F	
t _{VDET32}	Discharge overcurrent 2 detection delay time	V _{DD} = 3.6V, V _{RSENS} = 0V → V _{DET32} +0.005V, V ₋ = V _{RSENS}	t _{VDET32} ×0.75	t _{VDET32}	t _{VDET32} ×1.30	ms	F	

(1) Refer to *TEST CIRCUITS* for detail information.

(2) R5612LxxxxA/B/G only

(3) R5612LxxxxD/E/H only

R5612LxxxXX Electrical Characteristics (Continued)

(Ta = 25°C)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	Circuit (1)	
V _{SHORT1}	Short detection voltage 1	Detect rising edge of RSENS pin voltage, V _{DD} = 3.6 V, V _{RSENS} = V-	0.030 V ≤ V _{SHORT1} ≤ 0.120 V	V _{SHORT1} -0.004	V _{SHORT1} +0.004	V	F	
			0.120 V < V _{SHORT1} ≤ 0.200 V	V _{SHORT1} -0.005				V _{SHORT1} +0.005
t _{SHORT}	Short detection delay time (2)	V _{DD} = 3.6 V, V _{RSENS} = 0 V → 1 V V- = V _{RSENS}	210	280	380	μs	F	
V _{SHORT2}	Short detection voltage 2	Detect rising edge of V- pin voltage, V _{DD} = 3.6 V, V _{RSENS} = 0 V	V _{DD} × 0.850 -0.050	V _{DD} × 0.850	V _{DD} × 0.850 +0.050	V	F	
V _{REL3}	Discharge overcurrent release voltage	V _{DD} = 3.6 V, V _{RSENS} = 0 V	Auto Release1	V _{DD} × 0.800 -0.050	V _{DD} × 0.800 +0.050	V	F	
			Auto Release2	0.010	0.100			0.250
R _{SHORT}	Discharge overcurrent release resistance	Auto Release1: 3.2 V ≤ V _{DD} ≤ 4.4 V, V- = 2.93 V	6.5	10.0	13.5	kΩ	F	
		Auto Release2: V _{DD} = 3.6 V, V- = 0.2 V	20	45	70			
t _{REL3}	Discharge overcurrent release delay time	V _{DD} = 3.6 V, V- = 3.6 V → 0 V V _{RSENS} = 0 V	6.3	8.5	11.1	ms	F	
V _{DET4}	Charge overcurrent detection voltage	V _{DD} = 3.6 V, V- = V _{RSENS}	V _{DET4} -0.0010	V _{DET4}	V _{DET4} +0.0010	V	G	
t _{DET4}	Charge overcurrent detection delay time	V _{DD} = 3.6 V, V _{RSENS} = 0 V → -0.5 V, V- = V _{RSENS}	t _{DET4} × 0.75	t _{DET4}	t _{DET4} × 1.30	ms	G	
V _{REL4}	Charge overcurrent release voltage	V _{DD} = 3.6 V, V _{RSENS} = 0 V	0.010	0.100	0.250	V	G	
t _{REL4}	Charge overcurrent release delay time	V _{DD} = 3.6 V, V- = -0.5 V → 1 V V- = V _{RSENS}	3.0	4.0	5.2	ms	G	
V _{OL1}	COU _T pin NMOS ON voltage	I _{OL} = 50 μA, V _{DD} = 4.55 V		0.4	0.5	V	H	
V _{OH1}	COU _T pin PMOS ON voltage	I _{OH} = -50 μA, V _{DD} = 3.9 V	3.4	3.7		V	I	
V _{OL2}	DOU _T pin NMOS ON voltage	I _{OL} = 50 μA, V _{DD} = 1.9 V		0.2	0.5	V	J	
V _{OH2}	COU _T pin PMOS ON voltage	I _{OH} = -50 μA, V _{DD} = 3.9 V	3.4	3.7		V	K	
I _{DD}	Supply current	V _{DD} = 3.9 V, V- = 0 V	Support for the 0 V battery charging "Inhibition" and the discharge overcurrent detection with two levels.		2.5	4.8	μA	L
			Except for the above support		2.0	4.0		
I _{STANDBY}	Standby current	V _{DD} = 1.9 V	V _{DET2} : Auto Release			0.2	μA	L
			V _{DET2} : Latch			0.04		

(1) Refer to *Test Circuits* for detail information.(2) Short release delay time 1 is the same value as t_{REL3}.

The specifications are guaranteed by design engineering at $-20^{\circ}\text{C} \leq T_a \leq 60^{\circ}\text{C}$.

R5612LxxxXX Electrical Characteristics

(-20°C ≤ Ta ≤ 60°C)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	Circuit (1)	
V_{DD1}	Operating input voltage	$V_{DD}-V_{SS}$	1.5		5.0	V	A	
V_{STCHG}	Minimum charging voltage for 0 V-battery charger ⁽²⁾	$V_{DD}-V_{-}$, $V_{DD}-V_{SS} = 0\text{ V}$			1.8	V	A	
V_{NOCHG}	0 V-battery Charging Inhibition Voltage ⁽³⁾	$V_{DD}-V_{SS}$, $V_{DD}-V_{-} = 4\text{ V}$	V_{NCHG} -0.30	V_{NCHG}	V_{NCHG} +0.30	V	A	
V_{DET1}	Overcharge detection voltage	$R1 = 330\Omega$	V_{DET1} -0.025	V_{DET1}	V_{DET1} +0.025	V	B	
V_{REL1}	Overcharge release voltage	$R1 = 330\Omega$	V_{REL1} -0.055	V_{REL1}	V_{REL1} +0.055	V	B	
t_{VDET1}	Overcharge detection delay time	$V_{DD} = 3.6\text{ V} \rightarrow V_{DET1}+0.1\text{ V}$	t_{VDET1} $\times 0.70$	t_{VDET1}	t_{VDET1} $\times 1.40$	ms	C	
t_{VREL1}	Overcharge release delay time	$V_{DD} = 4.8\text{ V}$ $\rightarrow V_{REL1}-0.1\text{ V}$	$t_{VREL1} = 1.2\text{ms}$	0.5	1.2	3.0	ms	C
			$t_{VREL1} = 16\text{ms}$	8	16	40		
V_{DET2}	Overdischarge detection voltage	Detect falling edge of supply voltage	V_{DET2} -0.055	V_{DET2}	V_{DET2} +0.055	V	D	
V_{REL2}	Overdischarge release voltage	Detect rising edge of supply voltage	V_{REL2} -0.065	V_{REL2}	V_{REL2} +0.105	V	E	
t_{VDET2}	Overdischarge detection delay time	$V_{DD} = V_{DET2}+0.15\text{V} \rightarrow V_{DET2}-0.1\text{V}$	t_{VDET2} $\times 0.70$	t_{VDET2}	t_{VDET2} $\times 1.40$	ms	D	
t_{VREL2}	Overdischarge release delay time	$V_{DD} = V_{DET2}-0.2\text{V} \rightarrow V_{REL2}+0.25\text{V}$	0.84	1.20	2.00	ms	E	
V_{CHGDET}	Charger Connection Detection Voltage	$V_{DD} = V_{DET2}+0.020\text{ V}$, $V_{RSENS} = 0\text{ V}$	0.400	0.800	1.200	V	A	
V_{DET31}	Discharge overcurrent detection voltage 1	$V_{DD} = 3.6\text{ V}$, $V_{-} = V_{RSENS}$	V_{DET31} -0.0015	V_{DET31}	V_{DET31} +0.0015	V	F	
t_{VDET31}	Discharge overcurrent 1 detection delay time	$V_{DD} = 3.6\text{ V}$, $V_{RSENS} = 0\text{ V} \rightarrow V_{DET31}+0.005\text{ V}$ $V_{-} = V_{RSENS}$	t_{VDET31} $\times 0.75$	t_{VDET31}	t_{VDET31} $\times 1.35$	ms	F	
V_{DET32}	Discharge overcurrent detection voltage 2	$V_{DD} = 3.6\text{ V}$, $V_{-} = V_{RSENS}$	V_{DET32} -0.0025	V_{DET32}	V_{DET32} +0.0025	V	F	
t_{VDET32}	Discharge overcurrent 2 detection delay time	$V_{DD} = 3.6\text{ V}$, $V_{RSENS} = 0\text{ V} \rightarrow V_{DET32}+0.005\text{ V}$ $V_{-} = V_{RSENS}$	t_{VDET32} $\times 0.70$	t_{VDET32}	t_{VDET32} $\times 1.40$	ms	F	

⁽¹⁾ Refer to *Test Circuits* for detail information.

⁽²⁾ R5612LxxxxA/B/G only

⁽³⁾ R5612LxxxxD/E/H only

R5612LxxxXX Electrical Characteristics (Continued)

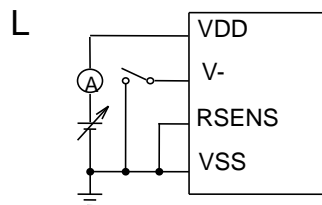
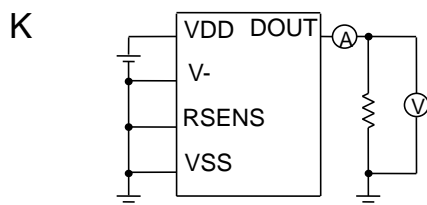
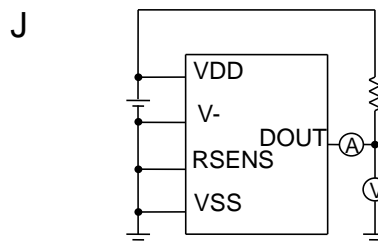
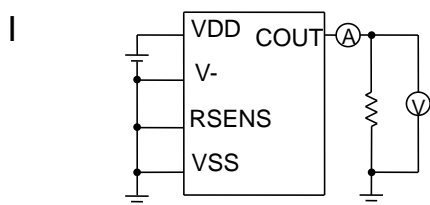
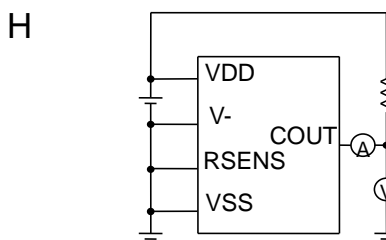
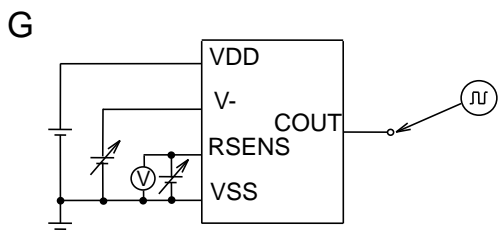
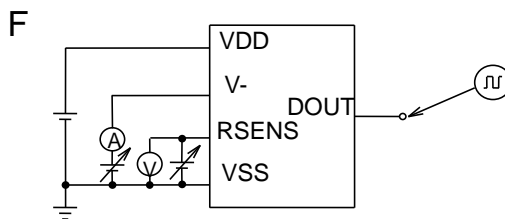
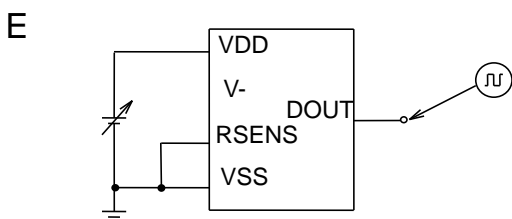
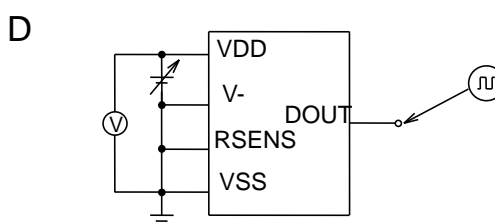
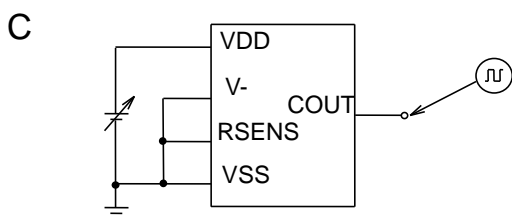
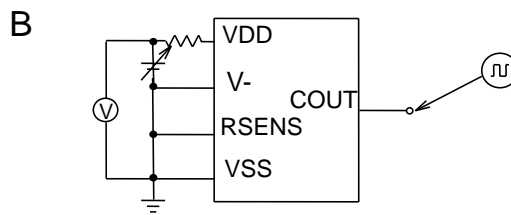
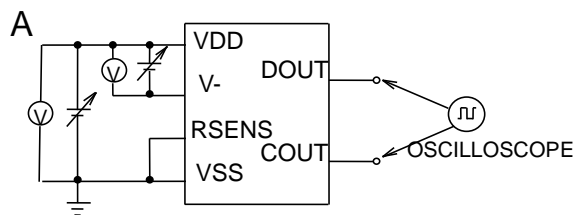
(-20°C ≤ Ta ≤ 60°C)

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit	Circuit (1)
V _{SHORT1}	Short detection voltage 1	Detect rising edge of RSENS pin voltage V _{DD} = 3.6 V, V _{RSENS} = V-	0.030V ≤ V _{SHORT1} ≤ 0.120V	V _{SHORT1} -0.005	V _{SHORT1}	V _{SHORT1} +0.005	V	F
			0.120V < V _{SHORT1} ≤ 0.200V	V _{SHORT1} -0.008		V _{SHORT1} -0.008		
t _{SHORT}	Short detection delay time (2)	V _{DD} = 3.6 V, V _{RSENS} = 0 V → 1 V V- = V _{RSENS}		175	280	420	μs	F
V _{SHORT2}	Short detection voltage 2	Detect rising edge of V- pin voltage, V _{DD} = 3.6V, V _{RSENS} = 0V		V _{DD} ×0.850 -0.100	V _{DD} ×0.850	V _{DD} ×0.850 +0.100	V	F
V _{REL3}	Discharge overcurrent release voltage	V _{DD} = 3.6 V, V _{RSENS} = 0 V	Auto Release1	V _{DD} ×0.800 -0.100	V _{DD} ×0.800	V _{DD} ×0.800 +0.100	V	F
			Auto Release2	0.000	0.100	0.300		
R _{SHORT}	Discharge overcurrent release resistance	Auto Release1: 3.2 V ≤ V _{DD} ≤ 4.4 V, V- = 2.93 V		5.5	10.0	14.5	kΩ	F
		Auto Release2: V _{DD} = 3.6 V, V- = 0.2 V		17.1	45.0	71.0		
t _{REL3}	Discharge overcurrent release delay time	V _{DD} = 3.6 V, V- = 3.6 V → 0 V V _{RSENS} = 0 V		5.95	8.5	12.0	ms	F
V _{DET4}	Charge overcurrent detection voltage	V _{DD} = 3.6 V, V- = V _{RSENS}		V _{DET4} -0.0015	V _{DET4}	V _{DET4} +0.0015	V	G
t _{VDET4}	Charge overcurrent detection delay time	V _{DD} = 3.6 V, V _{RSENS} = 0V → -0.5V, V- = V _{RSENS}		t _{VDET4} ×0.70	t _{VDET4}	t _{VDET4} ×1.40	ms	G
V _{REL4}	Charge overcurrent release voltage	V _{DD} = 3.6 V, V _{RSENS} = 0 V		0.000	0.100	0.300	V	G
t _{VREL4}	Charge overcurrent release delay time	V _{DD} = 3.6 V, V- = -0.5 V → 1 V V- = V _{RSENS}		2.8	4	5.6	ms	G
V _{OL1}	COU _T pin NMOS ON voltage	I _{OL} = 50μA, V _{DD} = 4.55 V			0.4	0.5	V	H
V _{OH1}	COU _T pin PMOS ON voltage	I _{OH} = -50μA, V _{DD} = 3.9 V		3.4	3.7		V	I
V _{OL2}	DOU _T pin NMOS ON voltage	I _{OL} = 50μA, V _{DD} = 1.9 V			0.2	0.5	V	J
V _{OH2}	COU _T pin PMOS ON voltage	I _{OH} = -50μA, V _{DD} = 3.9 V		3.4	3.7		V	K
I _{DD}	Supply current	V _{DD} = 3.9 V, V- = 0 V	Support for the 0 V battery charging "Inhibition" and the discharge overcurrent detection with two levels.		2.5	6.0	μA	L
			Except for the above support		2.0	5.0		
I _{STANDBY}	Standby current	V _{DET2} : Auto Release, V _{DD} = 1.6 V				0.3	μA	L
		V _{DET2} : Latch, V _{DD} = 1.9 V				0.1		

(1) Refer to TEST CIRCUITS for detail information.

(2) Short release delay time 1 is the same value as t_{VREL3}.

Test Circuits



THEORY OF OPERATION

Overcharge Protection

When the overcharge detection delay time (t_{VDET1}) passes under the condition that the VDD pin voltage (V_{DD}) exceeds the overcharge detection voltage (V_{DET1}), this IC enters the overcharge state.

In this state, the COUT pin becomes Low, and the charge control FET is turned off to stop charging. The V- pin voltage (V_-) increases by the Vf voltage (Vf) of the internal parasitic diode than the VSS pin voltage (V_{SS}) because the discharge current flows via the parasitic diode even when the charge control FET is off.

A release from the overcharge state must meet the following pin conditions and delay time according to the selected release type.

Type	Pin Conditions	Delay Time
Auto Release	$V_- < V_{REL4}$ and $V_{DD} < V_{REL1}$ or $V_- > V_{REL4}$ and $V_{DD} < V_{DET1}$	t_{VREL1}
Latch	$V_- > V_{REL4}$ and $V_{DD} < V_{DET1}$	t_{VREL1}

Overdischarge Protection

When the overdischarge detection delay time (t_{VDET2}) passes under the condition that the VDD pin voltage (V_{DD}) falls below the overdischarge detection voltage (V_{DET2}), this IC enters the overdischarge state.

In this state, the DOUT pin becomes Low, and the discharge control FET is turned off to stop discharging. The V- pin voltage (V_-) decreases by the Vf voltage (Vf) of the internal parasitic diode than the VSS pin voltage (V_{SS}) because the charge current flows via the parasitic diode even when the discharge control FET is off.

In addition, when V- is pulled up to V_{DD} level and exceeds the charger detection voltage (V_{CHGDET}), the IC enters the standby state. It results in reducing the consumption current to a minimum.

A release from the overdischarge state must meet the following pin conditions and delay time according to the selected release type.

Type	Pin Conditions	Delay Time
Auto Release	$V_- > V_{CHGDET}$ and $V_{DD} > V_{REL2}$ or $V_- < V_{CHGDET}$ and $V_{DD} > V_{DET2}$	t_{VREL2}
Latch	$V_- < V_{CHGDET}$ and $V_{DD} > V_{DET2}$	t_{VREL2}

Discharge Overcurrent Protection

In order to monitor a discharge current, this IC measures a voltage difference of the sense resistor (R_{SENS}) connected between the RSENS and the VSS pins to detect the current value.

This IC has two levels of the discharge overcurrent detection voltage $1/2 (V_{\text{DET31}} / V_{\text{DET32}})$. When the discharge overcurrent detection delay time (t_{VDET31}) passes under the condition that the discharge current, which is converted through R_{SENS} for current-to-voltage conversion, exceeds V_{DET31} , this IC enters the discharge overcurrent state. In a case where V_{DET32} is enabled, this IC enters the discharge overcurrent state when the discharge overcurrent detection delay time (t_{VDET32}) passes under the condition exceeding V_{DET32} .

In this state, the DOUT pin becomes Low, and the discharge control FET is turned off to shut off the discharge current.

A release from the discharge overcurrent state must meet the following pin condition and delay time according to the selected release type.

Type	Pin Condition	Delay Time	Remarks
Auto Release	$V^- < V_{\text{REL3}}$	t_{VREL3}	V^- is pulled down to the VSS level inside the IC. <small>Note</small>

Note: It is possible to release the abnormal condition of the load connected to the battery pack. When the discharge overcurrent release delay time (t_{VREL3}) passes under the condition V^- falls below V_{REL3} , this IC releases from the discharge overcurrent state. V^- can be expressed by the following equation.

$$V^- = V_{\text{CELL}} \times R_{\text{SHORT}} / (R_{\text{SHORT}} + R_{V^-} + R_{\text{LOAD}})$$

- V_{CELL} : Battery voltage
- R_{SHORT} : Discharge overcurrent release resistance
- R_{V^-} : External resistor for V^- pin
- R_{LOAD} : Load resistance to a battery pack

Short-circuit Current Protection

In order to monitor a short-circuit current, this IC measures a voltage difference of the sense resistor (R_{SENS}) connected between the RSENS and the VSS pins to detect the current value. When the short-circuit detection delay time (t_{SHORT}) passes under the condition that the short-circuit current, which is converted through R_{SENS} for current-to-voltage conversion, exceeds the short-circuit detection voltage (V_{SHORT}), this IC enters the short-circuit state.

In this state, the DOUT pin becomes Low, and the discharge control FET is turned off to shut off the short-circuit current.

A release from the short-circuit state must meet the same condition and delay time as the discharge overcurrent protection.

Charge Overcurrent Protection

In order to monitor a charge current, this IC measures a voltage difference of the sense resistor (R_{SENS}) connected between the RSENS and the VSS pins to detect the current value. When the charge overcurrent detection delay time (t_{VDET4}) passes under the condition that the charge current, which is converted through R_{SENS} for current-to-voltage conversion, falls below the charge overcurrent detection voltage (V_{DET4}), this IC enters the charge overcurrent state.

In this state, the COUT pin becomes Low, and the charge control FET is turned off to shut off the charge current.

A release from the charge overcurrent state must meet the following pin condition and delay time according to the selected release type.

Type	Pin Condition	Delay Time	Remarks
Auto Release	$V^- > V_{\text{REL4}}$	t_{VREL4}	V^- is pulled up to the VDD level inside the IC. ^{Note}

Note: By disconnecting the charger, this IC releases from the charge overcurrent state.

0 V Battery Charging

This IC has the selectable charging function for the battery discharged to 0 V.

0 V Battery Charge Function “Permission”

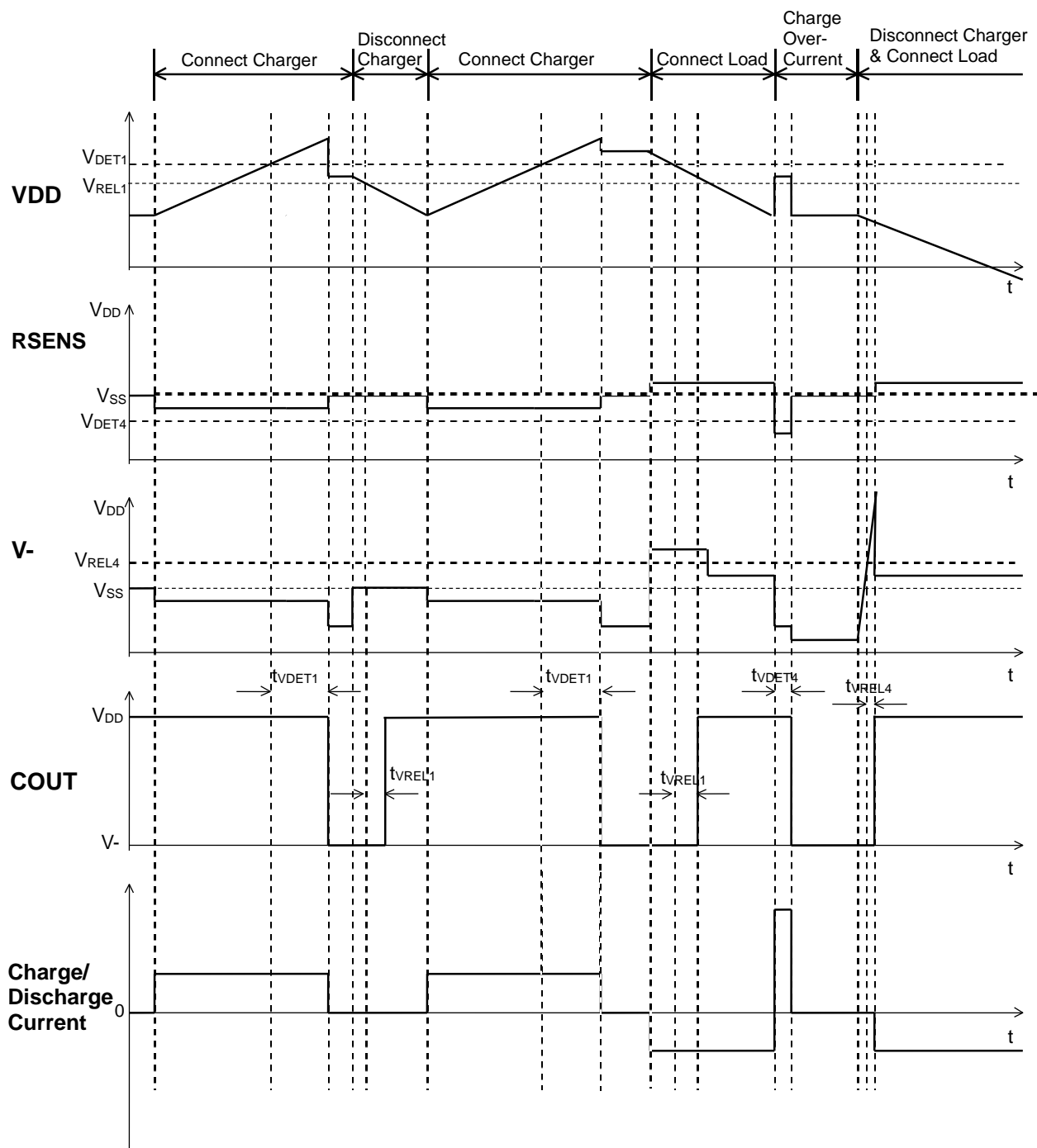
This function allows to charge to the 0 V battery by connecting the charger with the minimum charging voltage (V_{STCHG}) and more.

0 V Battery Charge Function “Prohibition”

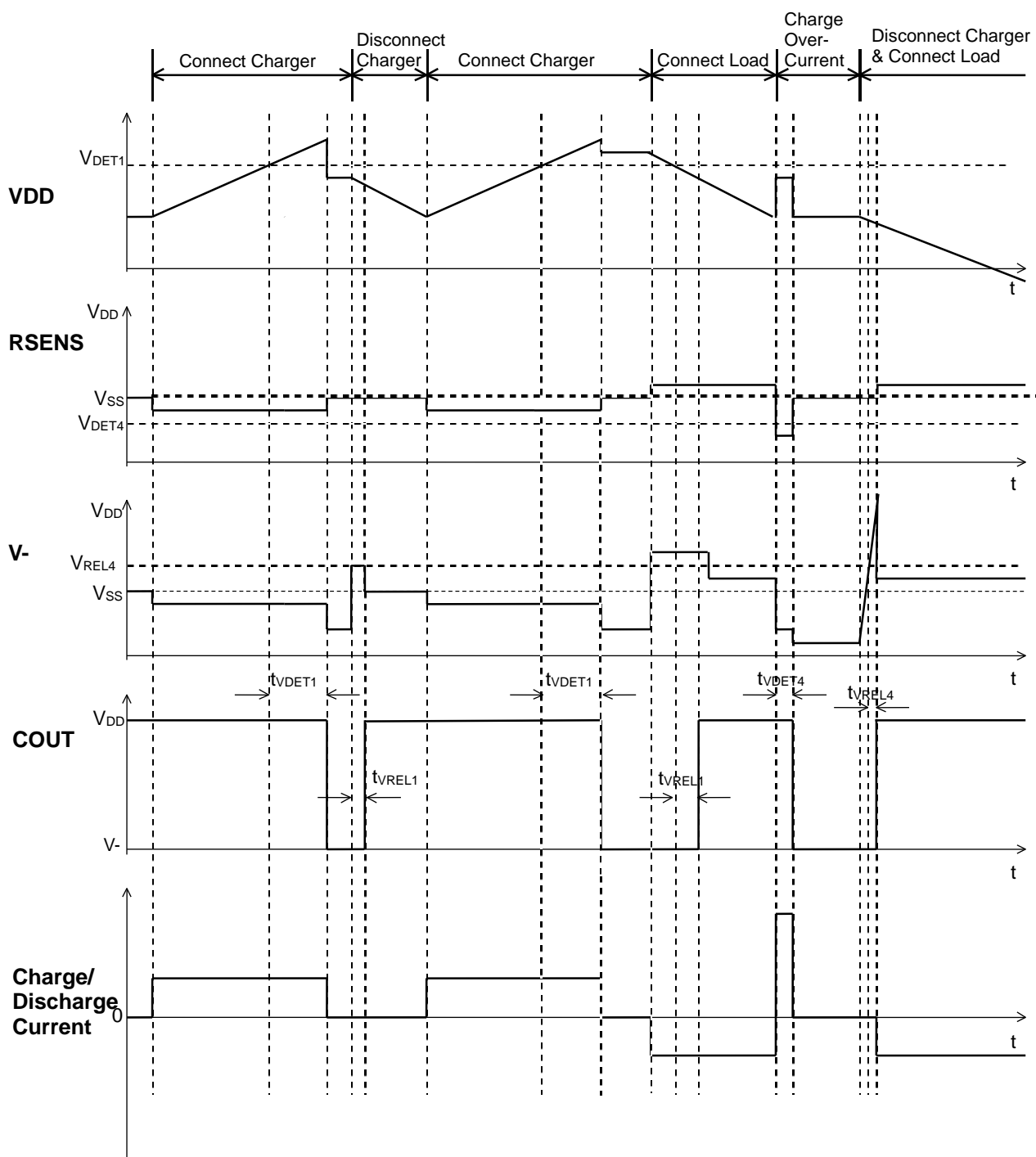
This function inhibits to charge to the battery with the 0 V-battery charging inhibition voltage (V_{NOCHG}) or less even if connecting the charger.

Timing Charts

Overcharge voltage and Overcharge current

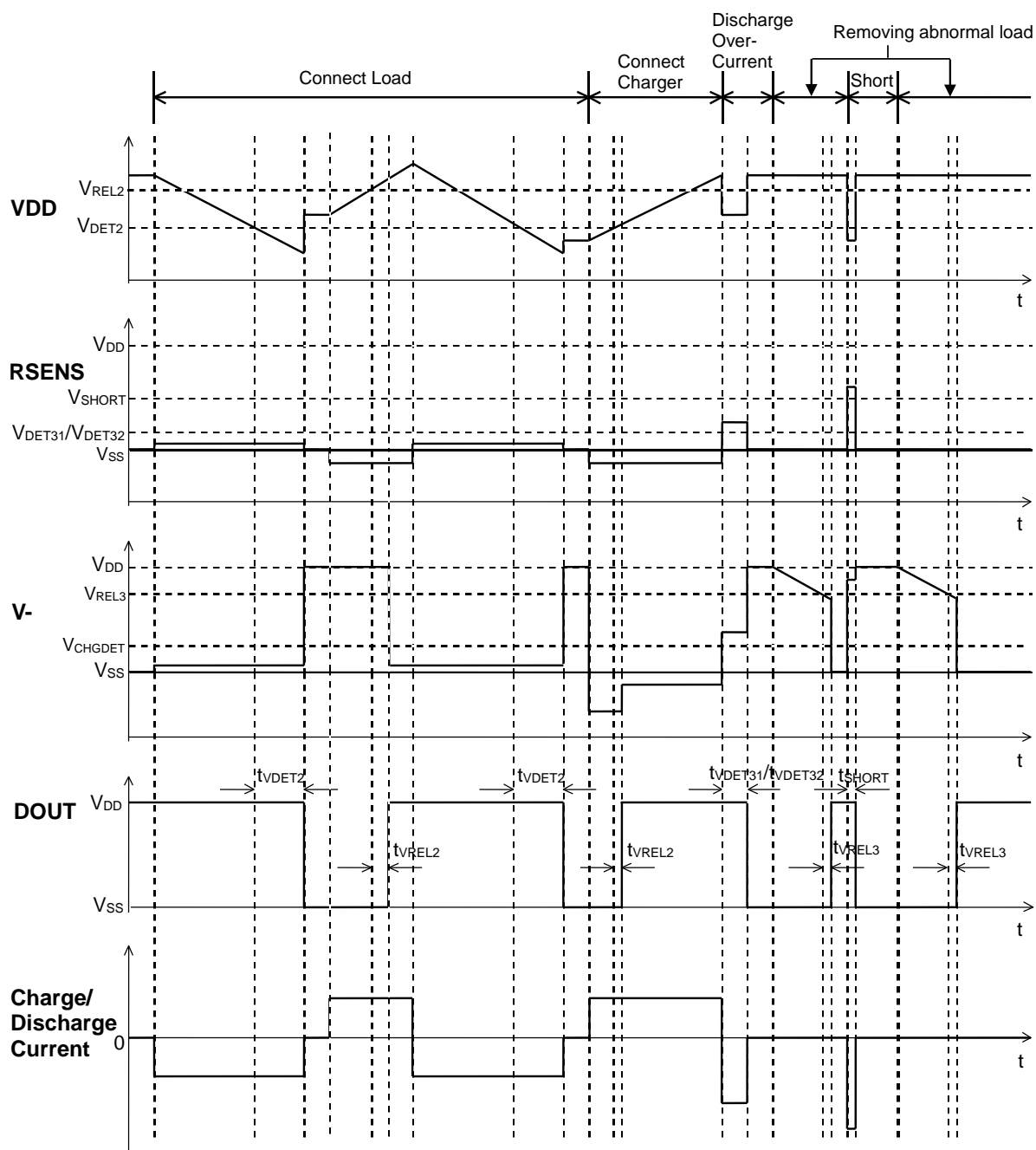


Overcharge (Auto Release type) Timing Diagram

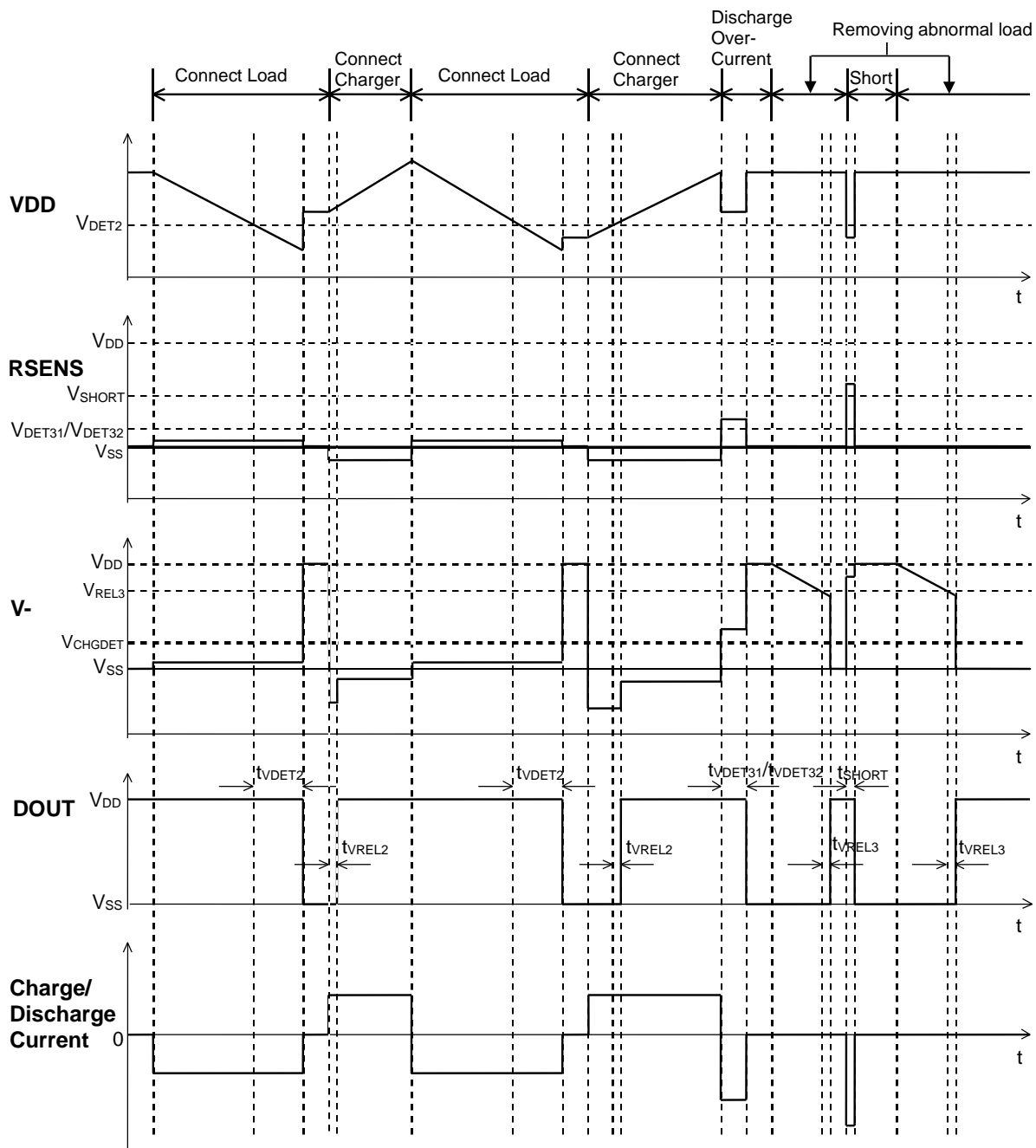


Overcharge (Latch type) Timing Diagram

Overdischarge / Discharge overcurrent and Short-circuit



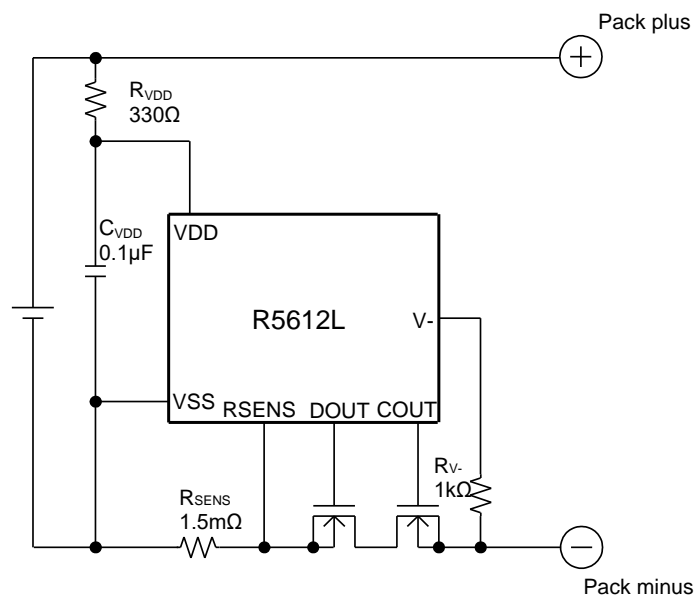
Overdischarge / Discharge Overcurrent (Auto Release type), Short-circuit Timing Diagram



Overdischarge / Discharge Overcurrent (Latch type), Short-circuit Timing Diagram

Application Information

Typical Application Circuit



R5612LxxxXX Typical Application Circuit

External Components

Symbol	Min.	Typ.	Max.
Resistor			
$R_{VDD}^{(1)}$		330Ω	1kΩ
$R_{V-}^{(1)}$	—	1kΩ	1.3kΩ
R_{SENS}	—	1.5mΩ	20mΩ
Capacitor			
C_{VDD}	0.01μF	0.1μF	1μF

⁽¹⁾ The total resistance of R_{VDD} and R_{V-} must be 1kΩ or more.

Technical Notes on External Components

- The voltage fluctuation is stabilized with R_{VDD} and C_{VDD} . If a R_{VDD} is too large, the detection voltage rises by the conduction current at detection. To stabilize the operation, it is recommended to use a resistor of $1k\Omega$ or less for R_{VDD} and a capacitor of $0.01 \mu F$ to $1.0 \mu F$ for C_{VDD} .
- R_{VDD} and R_{V-} serve as a current limit resistor when the battery pack is charged with reversed polarity or a voltage of the connected charger is more than the absolute maximum rating. When using a small resistor for R_{VDD} and R_{V-} , the device's power dissipation might be exceeded. Therefore, a total of R_{VDD} and R_{V-} must be $1k\Omega$ or more. When using a large resistor for R_{V-} , the charger might not be released by re-connecting to the battery pack after the overdischarge detection. Therefore, R_{V-} must be $1.3 k\Omega$ or less. Production variation and temperature properties are included in the value. R_{SENS} is a resistor for sensing an overcurrent. If the resistance value is too large, power loss becomes also large. By the overcurrent, if the R_{SENS} is not appropriate, the power loss may be beyond the power dissipation of R_{SENS} . Choose an appropriate R_{SENS} according to the cell specification.
- The typical application circuit diagrams are just examples. This circuit performance largely depends on the PCB layout and external components. In the actual application, fully evaluation is necessary.
- If the positive terminal and the negative terminal of the battery pack are short even though the device has the short protection circuit, a large current may flow through the FET during the short detection delay time. Therefore, select an appropriate FET with large enough current capacitance in order to endure the large current during the delay time.

Selection of External Sense Resistor and MOSFET

Short mode is detected by the current base or the relation between V_{DD} at short and total on resistance of external MOSFETs for C_{OUT} and D_{OUT} . If short must be detected by the current base determined by V_{SHORT1} , V_{SHORT2} , and R_{SENS} , the next formula must be true, otherwise, the short current limit becomes $(V_{SHORT2}) / (R_{SENS} + R_{SS} (on))$.

$$\frac{V_{SHORT2}}{R_{SENS} + R_{SS}(on)} \geq \frac{V_{SHORT1}}{R_{SENS}}$$

V_{SHORT1} = Threshold value of detecting short circuit using R_{SENS} terminal [V]

V_{SHORT2} = Threshold value of detecting short circuit using V- terminal [V]

R_{SENS} : = External current sense resistance [Ω]

$R_{SS} (on)$ = external MOSFETs' total ON resistance [Ω]

In the short mode, a short current is determined by the relation between R_{SENS} and V_{SHORT} value.

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51.

Measurement Conditions

Item	Measurement Conditions
Environment	Mounting on Board (Wind Velocity = 0 m/s)
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)
Board Dimensions	76.2 mm × 114.3 mm × 1.6 mm
Copper Ratio	Outer Layer (First Layer): Less than 10% of 74.2 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 74.2 mm Square Outer Layer (Fourth Layer): Less than 10% of 74.2 mm Square
Through-holes	None

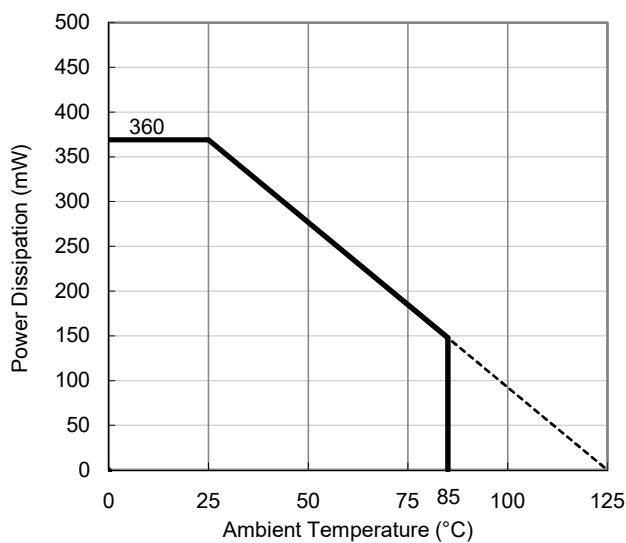
Measurement Result

(Ta = 25°C, Tjmax = 125°C)

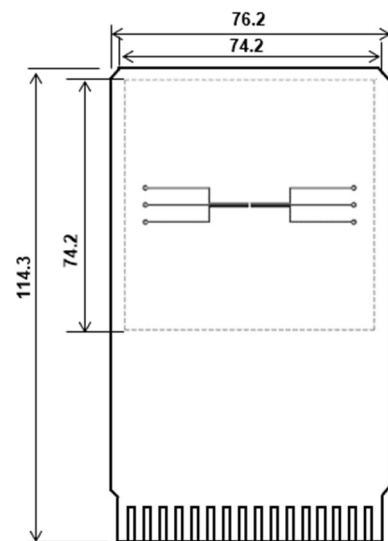
Item	Measurement Result
Power Dissipation	360 mW
Thermal Resistance (θ_{ja})	$\theta_{ja} = 271^\circ\text{C/W}$
Thermal Characterization Parameter (ψ_{jt})	$\psi_{jt} = 121^\circ\text{C/W}$

θ_{ja} : Junction-to-Ambient Thermal Resistance

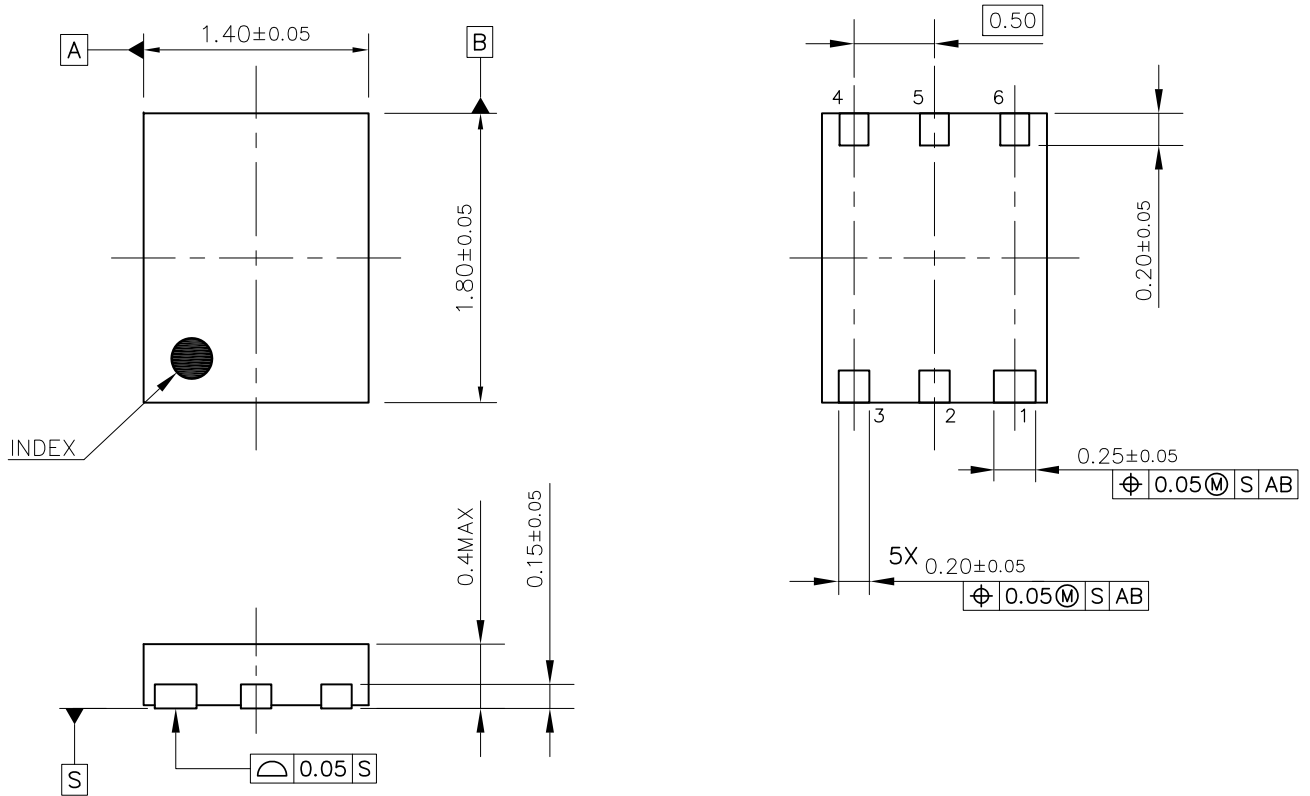
ψ_{jt} : Junction-to-Top Thermal Characterization Parameter



Power Dissipation vs. Ambient Temperature



Measurement Board Pattern



DFN1814-6C Package Dimensions (Unit: mm)



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